

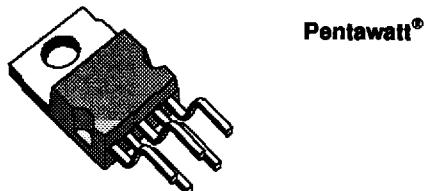
## 4A LINEAR DRIVER

- HIGH OUTPUT CURRENT (4A peak)
- HIGH CURRENT GAIN (10.000 typ.)
- OPERATION UP TO  $\pm 20$  V
- THERMAL PROTECTION
- SHORT CIRCUIT PROTECTION
- OPERATION WITHIN SOA
- HIGH SLEW-RATE (30 V/ $\mu$ s)

### DESCRIPTION

The L149 is a general purpose power booster in Pentawatt® package consisting of a quasi-complementary darlington output stage with the associated biasing system and inhibit facility.

The device is particularly suited for use with an operational amplifier inside a closed loop configuration to increase output current.



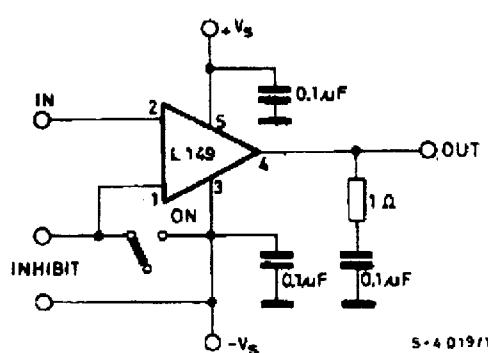
Pentawatt®

ORDER CODE : L149V

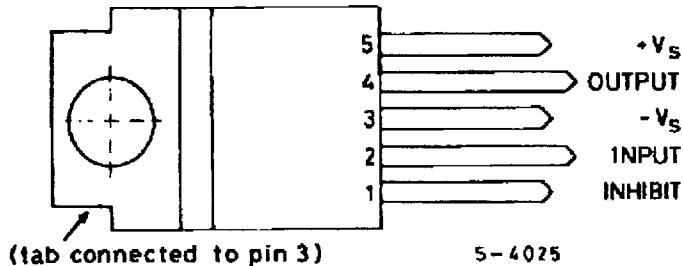
### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
$V_s$	Supply Voltage	$\pm 20$	V
$V_i$	Input Voltage		$V_s$
$V_5 - V_4$	Upper Power Transistor VCE	40	V
$V_4 - V_3$	Lower Power Transistor VCE	40	V
$I_o$	DC Output Current	3	A
$I_o$	Peak Output Current (internally limited)	4	A
$V_{INH}$	Input Inhibit Voltage	- $V_s + 5$ - $V_s - 1.5$	V
$P_{tot}$	Total Power Dissipation at $T_{case} = 75$ °C	25	W

### TEST CIRCUIT

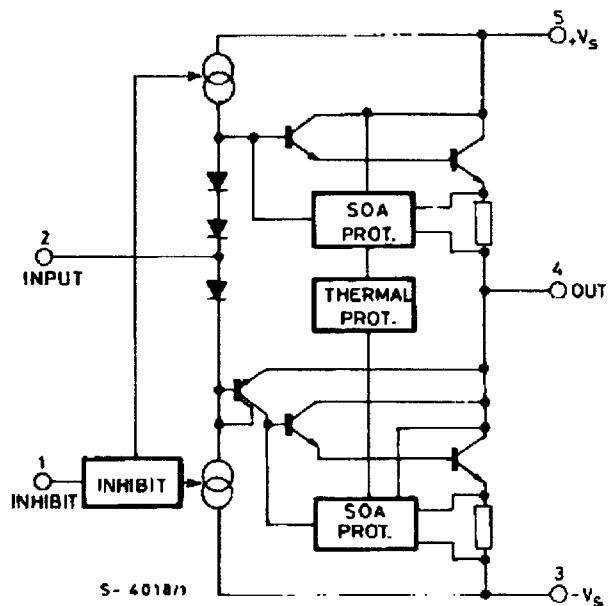


CONNECTION DIAGRAM (top view)



5-4025

SCHEMATIC DIAGRAM

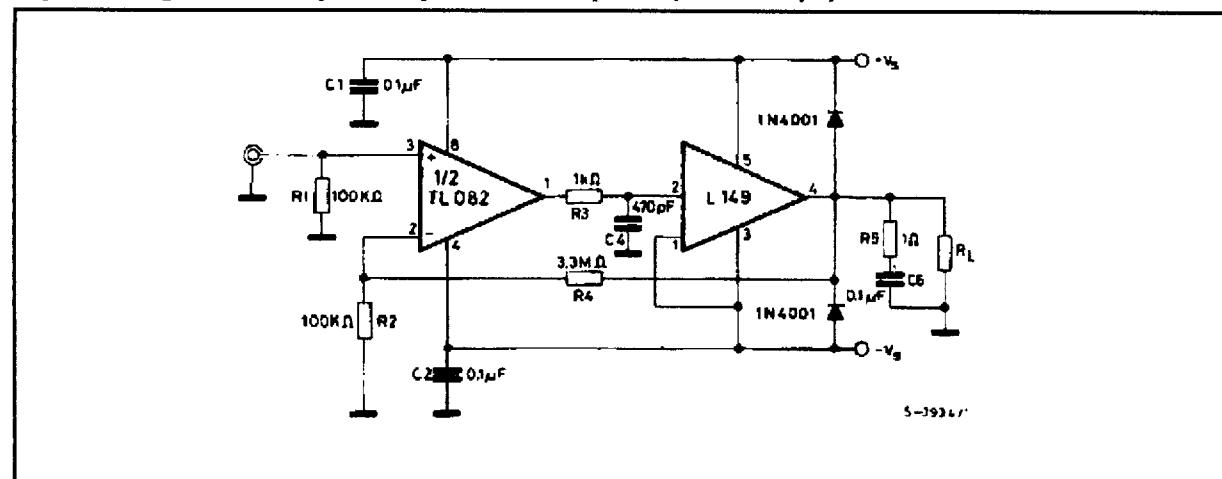


**THERMAL DATA**

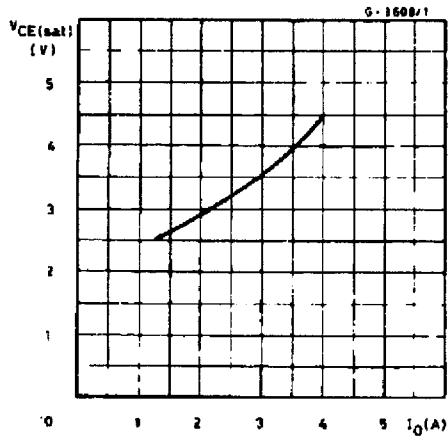
Symbol	Parameter	Value	Unit
R <sub>th-j-case</sub>	Thermal resistance junction-case	max 3	°C/W

**ELECTRICAL CHARACTERISTICS (T<sub>j</sub> = 25 °C, V<sub>s</sub> = ± 16V)**

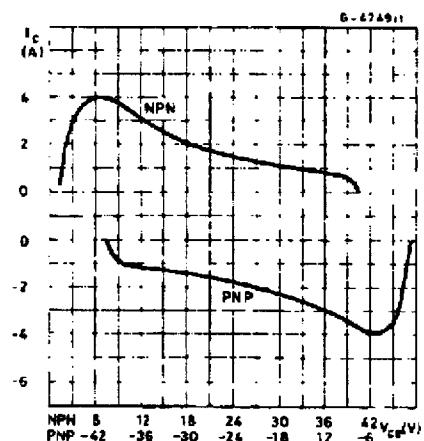
Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V <sub>s</sub>	Supply Voltage				± 20	V
I <sub>d</sub>	Quiescent Drain Current	V <sub>s</sub> = ± 16 V		30		mA
I <sub>in</sub>	Input current	V <sub>s</sub> = ± 16 V      V <sub>i</sub> = 0V		200	400	μA
h <sub>FE</sub>	DC current drain	V <sub>s</sub> = ± 16 V      I <sub>o</sub> = 3A	6000	10000		-
G <sub>v</sub>	Voltage gain	V <sub>s</sub> = ± 16 V      I <sub>o</sub> = 1.5A		1		-
V <sub>CEsat</sub>	Saturation voltage (for each transistor)	I <sub>o</sub> = 3A			3.5	V
V <sub>os</sub>	Input offset voltage	V <sub>s</sub> = ± 16 V			0.3	V
V <sub>INH</sub>	Inhibit input voltage (pins 1-3)	ON condition			± 0.3	V
		OFF condition	± 1.8			
R <sub>INH</sub>	Inhibit input resistance			2.0		KΩ
SR	Slew rate			30		V/μs
B	Power bandwidth	V <sub>o</sub> = ± 10V, d = 1%, R <sub>L</sub> = 8Ω		200		KHz

**APPLICATION INFORMATION****Figure 1. High slew-rate power operational amplifier (SR = 13V/μs)**

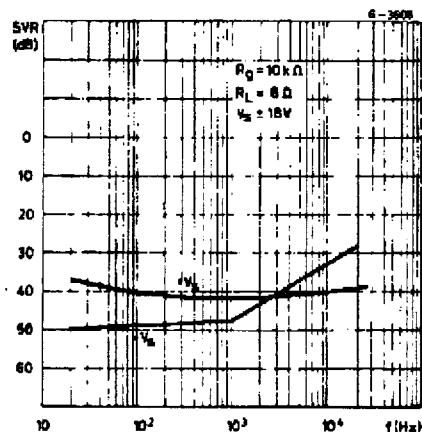
**Figure 2. Maximum saturation voltage vs. output current.**



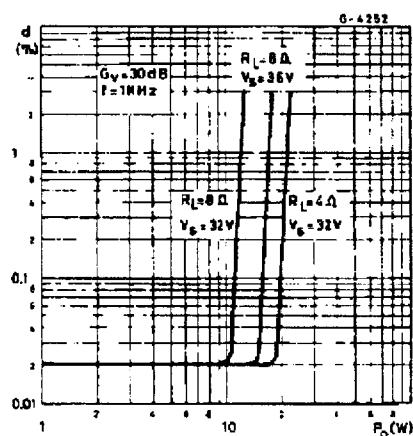
**Figure 3. Current limiting characteristics.**



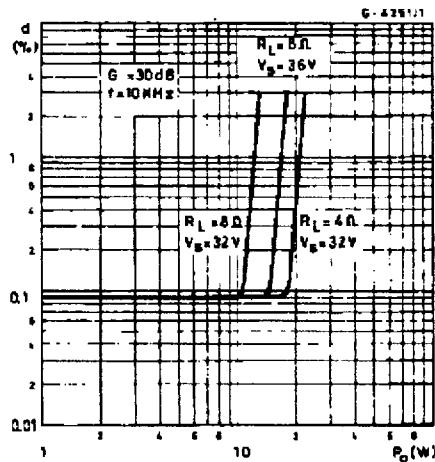
**Figure 4: Supply voltage rejection vs. frequency.**



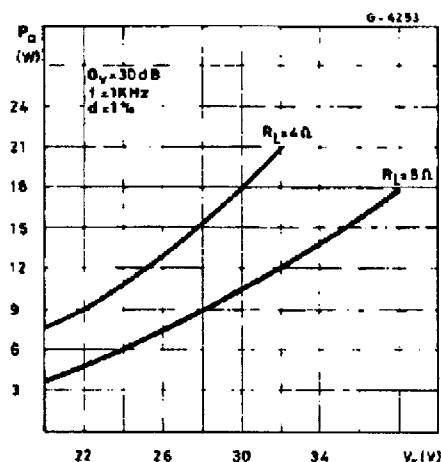
**Figure 5: Distortion vs. output power ( $f = 1\text{KHz}$ ).**



**Figure 6. Distortion vs. output power ( $f = 1\text{KHz}$ ).**

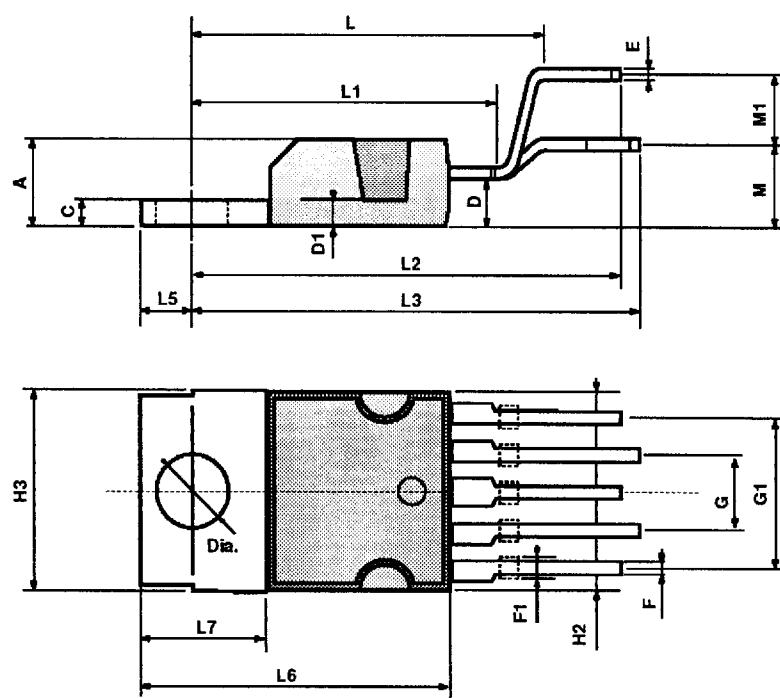


**Figure 7. Output power vs. supply voltage.**



## PENTAWATT PACKAGE MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			4.8			0.189
C			1.37			0.054
D	2.4		2.8	0.094		0.110
D1	1.2		1.35	0.047		0.053
E	0.35		0.55	0.014		0.022
F	0.8		1.05	0.031		0.041
F1	1		1.4	0.039		0.055
G		3.4		0.126	0.134	0.142
G1		6.8		0.260	0.268	0.276
H2			10.4			0.409
H3	10.05		10.4	0.396		0.409
L		17.85			0.703	
L1		15.75			0.620	
L2		21.4			0.843	
L3		22.5			0.886	
L5	2.6		3	0.102		0.118
L6	15.1		15.8	0.594		0.622
L7	6		6.6	0.236		0.260
M		4.5			0.177	
M1		4			0.157	
Dia	3.65		3.85	0.144		0.152



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